

Complementary power Darlingtons

Features

- Monolithic Darlingtons configuration
- Integrated antiparallel collector-emitter diode

Application

- Linear and switching industrial equipment

Description

The devices are manufactured in planar technology with “base island” layout and monolithic Darlingtons configuration. The resulting transistors show exceptional high gain performance coupled with very low saturation voltage.

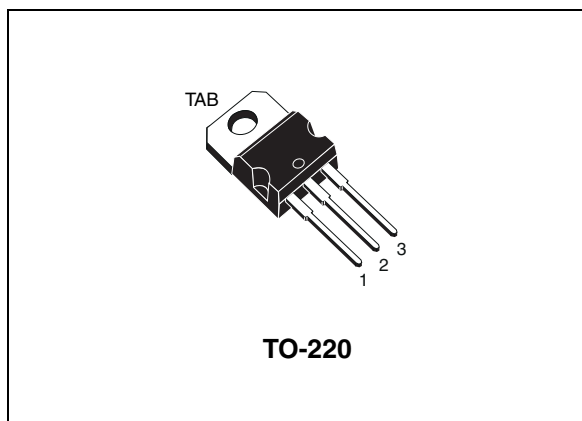


Figure 1. Internal schematic diagrams

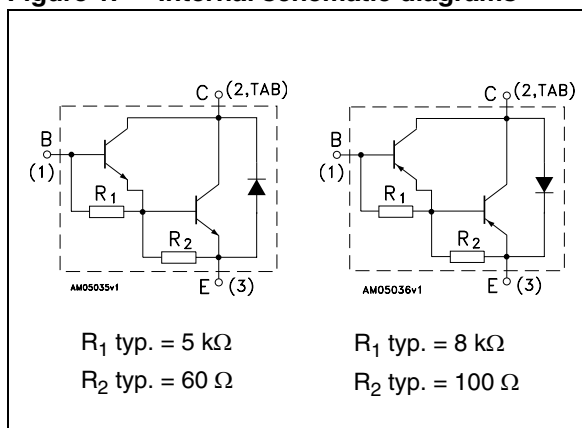


Table 1. Device summary

Part number	Marking	Polarity	Package	Packaging
TIP142T	TIP142T	NPN	TO-220	Tube
TIP147T	TIP147T	PNP		

1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	100	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	100	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	5	V
I_C	Collector current	10	A
I_{CM}	Collector peak current	20	A
I_B	Base current	0.5	A
P_{TOT}	Total dissipation at $T_{case} = 25\text{ °C}$	90	W
T_{STG}	Storage temperature	-65 to 150	°C
T_J	Max. operating junction temperature	150	°C

Note: For PNP type voltage and current are negative.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case	max 1.4	°C/W

2 Electrical characteristics

$T_{\text{case}} = 25\text{ °C}$; unless otherwise specified.

Table 4. Electrical characteristics

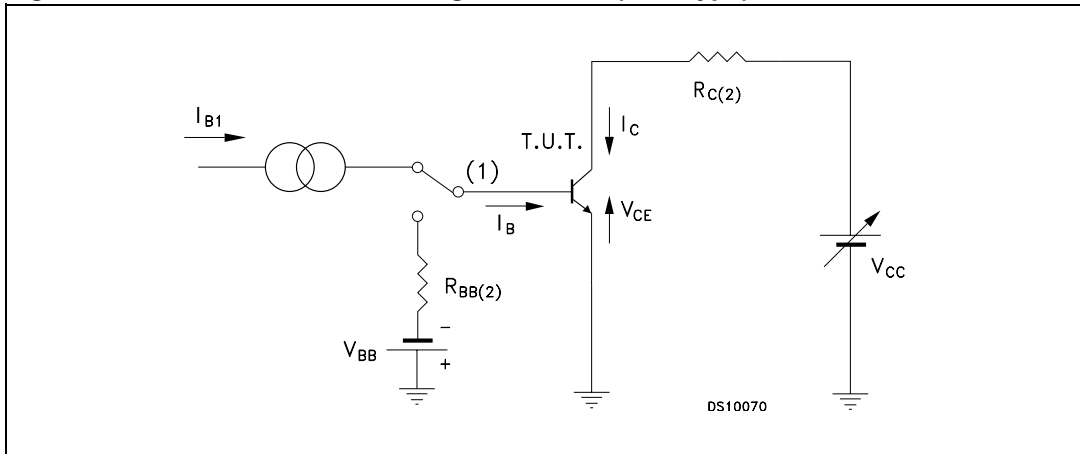
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_{\text{E}} = 0$)	$V_{\text{CB}} = 100\text{ V}$			1	mA
I_{CEO}	Collector cut-off current ($I_{\text{B}} = 0$)	$V_{\text{CE}} = 50\text{ V}$			2	mA
I_{EBO}	Emitter cut-off current ($I_{\text{C}} = 0$)	$V_{\text{EB}} = 5\text{ V}$			2	mA
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = 30\text{ mA}$	100			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 5\text{ A}$ $I_{\text{B}} = 10\text{ mA}$ $I_{\text{C}} = 10\text{ A}$ $I_{\text{B}} = 40\text{ mA}$			2 3	V V
$V_{\text{BE(on)}}^{(1)}$	Base-emitter on voltage	$I_{\text{C}} = 10\text{ A}$ $V_{\text{CE}} = 4\text{ V}$			3	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 5\text{ A}$ $V_{\text{CE}} = 4\text{ V}$ $I_{\text{C}} = 10\text{ A}$ $V_{\text{CE}} = 4\text{ V}$	1000 500			
t_{on} t_{off}	Resistive load Turn-on time Turn-off time	$I_{\text{C}} = 10\text{ A}$ $R_{\text{L}} = 3\text{ }\Omega$ $I_{\text{B1}} = -I_{\text{B2}} = 40\text{ mA}$		0.9 4		μs μs

1. Pulse test: pulse duration $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Note: For PNP type voltage and current are negative.

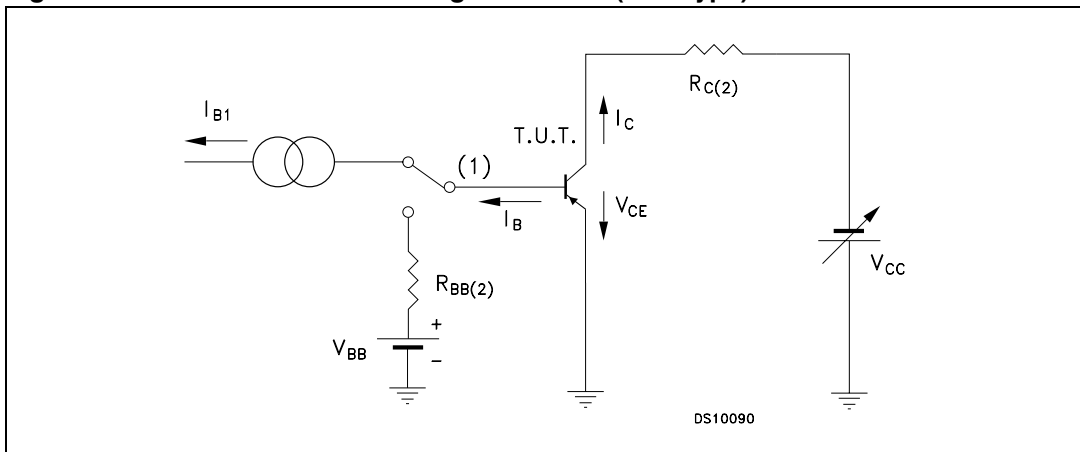
2.1 Test circuits

Figure 2. Resistive load switching test circuit (NPN type)



1. Fast electronic switch
2. Non-inductive resistor

Figure 3. Resistive load switching test circuit (PNP type)



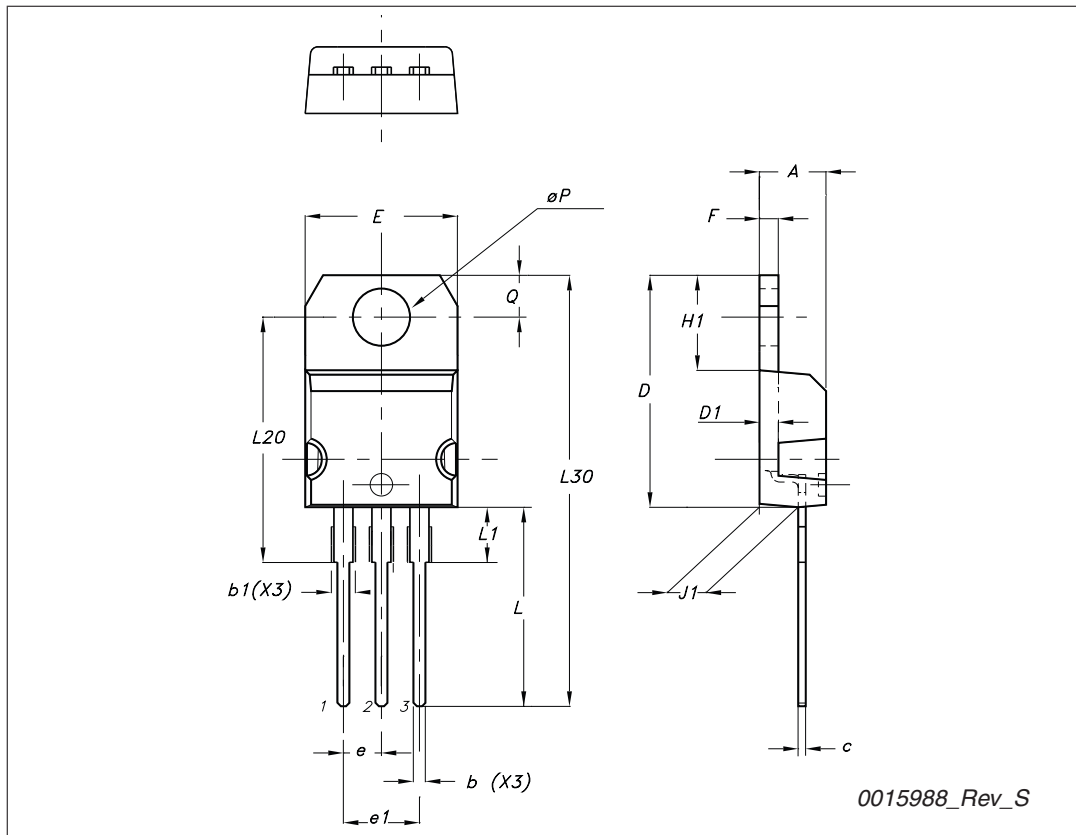
1. Fast electronic switch
2. Non-inductive resistor

3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



4 Revision history

Table 5. Document revision history

Date	Revision	Changes
21-Jun-2004	4	
20-May-2010	5	Technology change from epitaxial base to planar base island.